imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

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SURFACE MOUNT DUAL NPN SILICON TRANSISTORS





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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXT2222A type is a dual NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, and designed for small signal general purpose and switching applications.

MARKING CODE: X1P

MAXIMUM RATINGS: (T _A =25°C)	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	75	V
Collector-Emitter Voltage	VCEO	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Continuous Collector Current	IC	600	mA
Power Dissipation	PD	350	mW
Operating and Storage Junction Temperature	т _Ј , т _{stg}	-65 to +150	°C
Thermal Resistance	ΘJA	357	°C/W

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: (TA=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
ICBO	V _{CB} =60V		10	nA
ICBO	V _{CB} =60V, T _A =125°C		10	μΑ
ICEV	V _{CE} =60V, V _{EB} =3.0V		10	nA
IEBO	V _{EB} =3.0V		10	nA
BVCBO	Ι _C =10μΑ	75		V
BVCEO	I _C =10mA	40		V
BVEBO	I _E =10μA	6.0		V
V _{CE(SAT)}	I _C =150mA, I _B =15mA		0.3	V
VCE(SAT)	I _C =500mA, I _B =50mA		1.0	V
V _{BE} (SAT)	I _C =150mA, I _B =15mA	0.6	1.2	V
V _{BE(SAT)}	I _C =500mA, I _B =50mA		2.0	V
hFE	V _{CE} =10V, I _C =0.1mA	35		
hFE	V _{CE} =10V, I _C =1.0mA	50		
hFE	V _{CE} =10V, I _C =10mA	75		
hFE	V _{CE} =10V, I _C =150mA	100	300	
hFE	V _{CE} =1.0V, I _C =150mA	50		
hFE	V _{CE} =10V, I _C =500mA	40		
fT	V _{CE} =20V, I _C =20mA, f=100MHz	300		MHz
Cob	V _{CB} =10V, I _E =0, f=1.0MHz		8.0	pF
C _{ib}	V _{EB} =0.5V, I _C =0, f=1.0MHz		25	pF
h _{ie}	V _{CE} =10V, I _C =1.0mA, f=1.0kHz	2.0	8.0	kΩ
h _{ie}	V _{CE} =10V, I _C =10mA, f=1.0kHz	0.25	1.25	kΩ

R3 (12-February 2010)

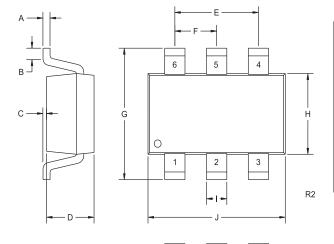




SURFACE MOUNT DUAL NPN SILICON TRANSISTORS

ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: (T _A =25°C unless otherwise noted)				
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h _{re}	V _{CE} =10V, I _C =1.0mA, f=1.0kHz		8.0	x10 ⁻⁴
h _{re}	V _{CE} =10V, I _C =10mA, f=1.0kHz		4.0	x10 ⁻⁴
h _{fe}	V _{CE} =10V, I _C =1.0mA, f=1.0kHz	50	300	
h _{fe}	V _{CE} =10V, I _C =10mA, f=1.0kHz	75	375	
h _{oe}	V _{CE} =10V, I _C =1.0mA, f=1.0kHz	5.0	35	μS
h _{oe}	V _{CE} =10V, I _C =10mA, f=1.0kHz	25	200	μS
rb'C _C	V _{CB} =10V, I _E =20mA, f=31.8MHz		150	ps
NF	V _{CE} =10V, I _C =100μA, R _S =1.0kΩ, f=1.0kHz		4.0	dB
t _d	V _{CC} =30V, V _{BE} =0.5V, I _C =150mA, I _{B1} =15mA		10	ns
t _r	V_{CC} =30V, V_{BE} =0.5V, I_{C} =150mA, I_{B1} =15mA		25	ns
t _s	V _{CC} =30V, I _C =150mA, I _{B1} =I _{B2} =15mA		225	ns
t _f	V _{CC} =30V, I _C =150mA, I _{B1} =I _{B2} =15mA		60	ns

SOT-26 CASE - MECHANICAL OUTLINE



6

Q1

× 0

1

5

2

4

Q2

3

DIMENSIONS					
	INCHES		MILLIMETERS		
SYMBOL	MIN	MAX	MIN	MAX	
A	0.004	0.007	0.11	0.19	
В	0.016	-	0.40	-	
С	-	0.004	-	0.10	
D	0.039	0.047	1.00	1.20	
E	0.074	0.075	1.88	1.92	
F	0.037	0.038	0.93	0.97	
G	0.102	0.118	2.60	3.00	
Н	0.059	0.067	1.50	1.70	
	0.016		0.41		
J	0.110	0.118	2.80	3.00	
SOT-26 (REV: R2)					

LEAD CODE:

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q24) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

MARKING CODE: X1P

R3 (12-February 2010)

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OUTSTANDING SUPPORT AND SUPERIOR SERVICES

PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- · Environmental regulation compliance
- Customer specific screening
- · Up-screening capabilities

· Custom product packing

Custom bar coding for shipments

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- · Custom product and package development

REQUESTING PRODUCT PLATING

- If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when 1. ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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